MPM1A800A120C5

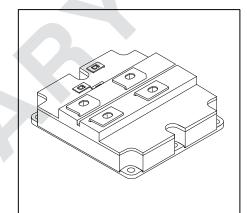
Preliminary Data Sheet Hybrid Power Module

This module is designed for use in switching applications. Each module utilizes advanced insulated gate bipolar transistors (IGBT) in a single configuration with a reverse-connected free-wheeling diode. Applications include AC motor control, UPS, and motion/servo control.

- 800 Amp, 1200 Volt IGBT Switch
- Low Inductance Package
- Convenient Package Outline
- Isolated Baseplate for Easy Heat Sinking
- Low VCE(sat)

Motorola Preferred Device

800 AMP, 1200 VOLT HYBRID POWER MODULE



PLASTIC PACKAGE PRELIMINARY

MAXIMUM DEVICE RATINGS (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
MAXIMUM RATED VALUES			•	
IGBT Reverse Voltage	VCES	1200	V	
Gate-Emitter Voltage	VGES	± 20	V	
Continuous IGBT Collector Current	IC	800	A	
Peak IGBT Collector Current	lC(pk)	1600	A	
Continuous Free-Wheeling Diode Current	lF	800	A	
Peak Free-Wheeling Diode Current	lF(pk)	1600	A	
Total Power Dissipation	P _{tot}	6300	W	
IGBT Junction Temperature Range	Тj	- 40 to +150	°C	
Free-Wheeling Diode Junction Temperature Range	Тj	- 40 to +125	°C	

This document contains information on a product under development. Motorola reserves the right to change or discontinue this product without notice.

Preferred devices are Motorola recommended choices for future use and best overall value.



REV 1

MAXIMUM DEVICE RATINGS (continued) (T_J = 25° C unless otherwise noted)

Rating		Symbol	Value	Unit
TOTAL MODULE				•
Isolation Voltage		VISO	3500	VAC
Maximum Junction Temperature		Tjmax	150	°C
Operating Temperature Range	Transistor Diode	T _{opr} T _{opr}	- 40 to + 150 - 40 to + 125	°C ℃
Storage Temperature Range		T _{stg}	- 40 to + 125	°C
Mounting Torque		-	3.0	Nm
Terminal Mounting Torque		-	8 – 10	Nm

ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OUTPUT INVERTER				•	•
Gate-Emitter Leakage Current (V _{CE} = 0 V, V _{GE} = \pm 20 V)	IGES	-	40	400	nA
Collector-Emitter Leakage Current (V _{CE} = 1200 V, V _{GE} = 0 V) T _J = 25°C T _J = 125°C	ICES	Ξ	5 20	25 -	mA mA
Gate-Emitter Threshold Voltage ($V_{CE} = V_{GE}$, $I_C = 80$ mA)	VGE(th)	4.5	5.5	6.5	V
Collector-Emitter Breakdown Voltage (I _C = 100 μ A, V _{GE} = 0)	V(BR)CES	1200	1300	-	V
Collector-Emitter Saturation Voltage (I _C = 1200 A, V _{GE} = 15 V) T _J = 25°C T _J = 125°C	VCE(SAT)		3.0 3.8		V V
Input Capacitance (V_{GE} = 0 V, V_{CE} = 25 V, f = 1.0 MHz)	Cies	-	160	-	nF
Fall Time – Inductive Load ($V_{CE} = 600 \text{ V}, \text{ I}_{C} = 1.2 \text{ kA}$)	t _{fi}	-	0.3	-	μs
Diode Forward Voltage (I _F = 1200 A, V _{GE} = 0 V)	VF	-	2.7	-	V
Thermal Resistance – IGBT (Each Die)	R _{θJC}	-	-	0.02	°C/W
Thermal Resistance – Free-Wheeling Diode (Each Die)	R _{θJC}	-	-	0.03	°C/W

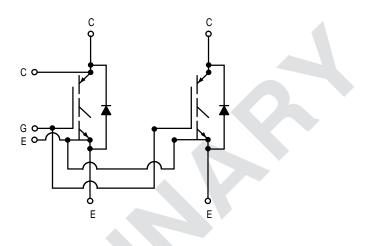
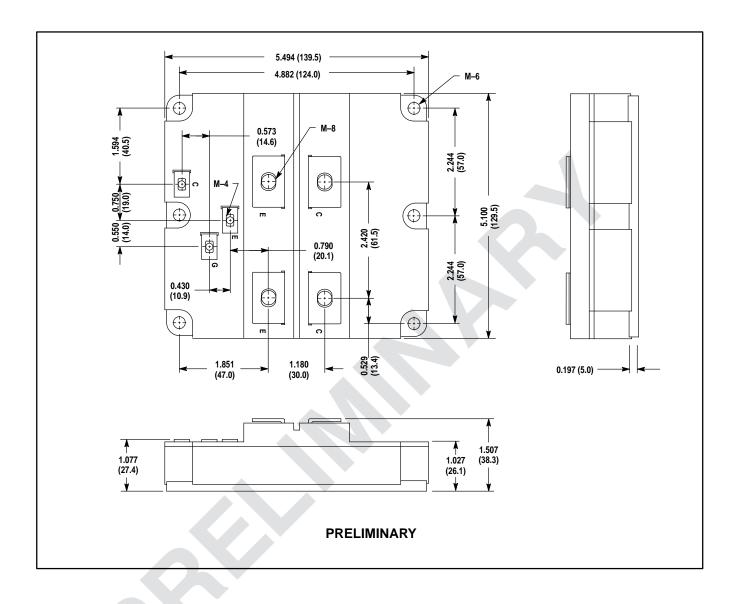


Figure 1.

PACKAGE DIMENSIONS



Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death Motorola was negligent regarding the design or manufacture of the part. Motorola and its an eregistered trademarks of Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447 JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki, 6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

 \Diamond



HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298

